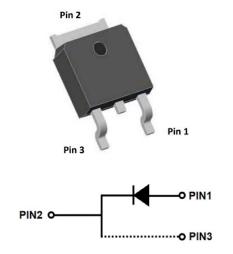


YJD112010DGH

RoHS COMPLIANT

Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _{F (135°C)}	13A
Q _c	58nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-252 Molding compound meets UL 94 V-0 flammability
- rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c =25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112010DGH
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _c =25°C			27
Continuous forward current @ T _c =135°C	I _F	А	13
Continuous forward current @ T _c =149°C			10
Non-repetitive peak forward surge current @ T_c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	90
Power Dissipation@ T _c =25°C	5	W	116
Power Dissipation@ T _c =110°C	P _{TOT}		50
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	40.5
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175



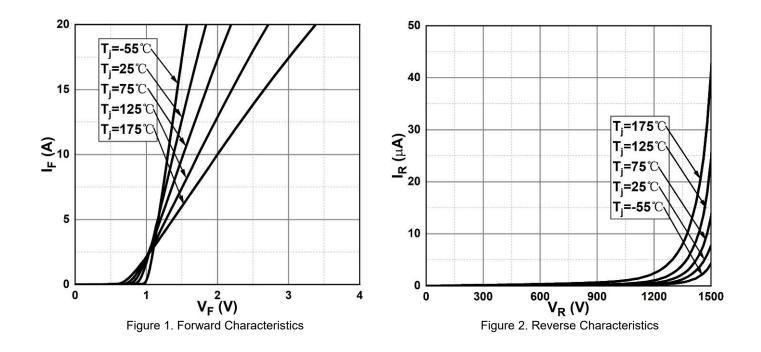
Electrical Characteristics

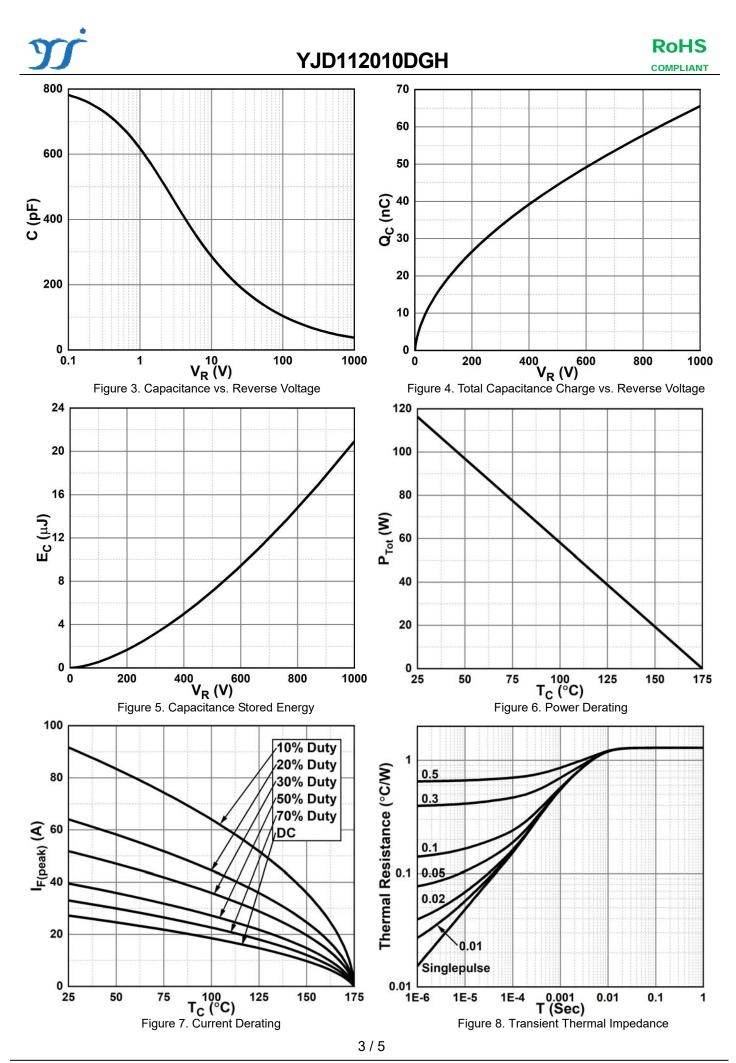
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward valtage dran		V	I _F =10A, T _j =25°C	1.38	1.55
Forward voltage drop	VF		I _F =10A, T _j =175°C	2	-
Povoroo lookago aurront		μΑ	V _R =1200V, T _j =25°C	0.5	20
Reverse leakage current	I _R		V _R =1200V, T _j =175°C	8	-
Total capacitive charge	Q _c	nC	$V_{\text{R}}{=}800\text{V},T_{j}{=}25^{\circ}\text{C}$, $Q_{\text{C}}{=}{\int_{0}}^{V_{\text{R}}}C(\text{V})\text{dV}$	58	-
	C t		V _R =0V, f=1MHZ	813	-
Total capacitance		pF	V _R =400V, f=1MHZ	54	-
			V _R =800V, f=1MHZ	40	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	15	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C /W	1.29

■Typical Characteristics

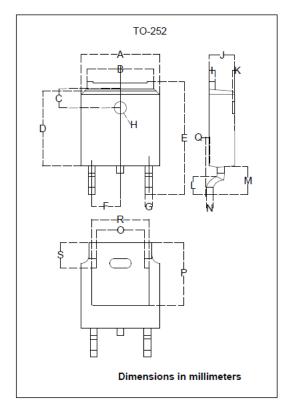




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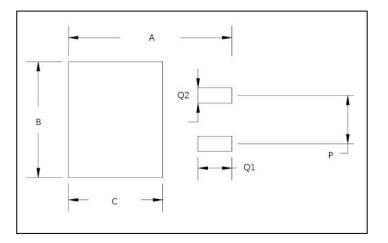


Outline Dimensions



TO-252		
Dim	Min	Max
Α	6.500	6.700
В	5.100	5.460
С	1.400	1.800
D	6.000	6.200
E	10.000	10.400
F	2.166	2.366
G	0.660	0.860
Н	Ф1.050	Ф1.350
I	0.460	0.580
J	2.200	2.400
К	0	0.300
L	0.890	2.290
М	2.730	3.080
N	0.430	0.580
0	4.20	4.95
Р	5.15	5.45
Q	0	0.2
R	4.50	5.10
S	1.60	2.40

■Suggested Pad Layout



Dim	Millimeters
А	11.4
В	6.74
С	6.23
Р	4.56
Q1	2.28
Q2	1.52



Disclaimer

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